

MICRO ELECTRONICS

2N718

NPN
SILICON
TRANSISTOR

DESCRIPTION

2N718 is NPN silicon planar transistor designed for medium power applications.

TO-18



CBE

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	VCER	40V
Collector-Base Voltage	VCBO	60V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	500mA
Continuous Power Dissipation	Pd	400mW
Operating & Storage Junction Temperature	Tj, Tstg	-65 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Emitter Breakdown Voltage	LVCER	40		V	IC=100μA REB=10ohm
Collector-Base Breakdown Voltage	BVCBO	60		V	IC=100μA IE=0
Emitter-Base Breakdown Voltage	BVEBO	5		V	IE=10μA IC=0
Collector Cutoff Current	ICBO		1000	nA	VCB=30V IE=0
D.C. Current Gain	HFE*	40	120		IC=150mA VCE=10V
Collector-Emitter Saturation Voltage	VCE(sat)*		1.5	V	IC=150mA IB=15mA
Base-Emitter Saturation Voltage	VBE(sat)*		1.3	V	IC=150mA IB=15mA
Current Gain Bandwidth Product	fT	50		MHz	IC=50mA VCE=10V f=20MHz

* Pulse test : pulse width < 300μs, duty cycle < 2%.



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This datasheet has been download from:

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Datasheets for electronics components.